



## R-C Thermal Model Parameters

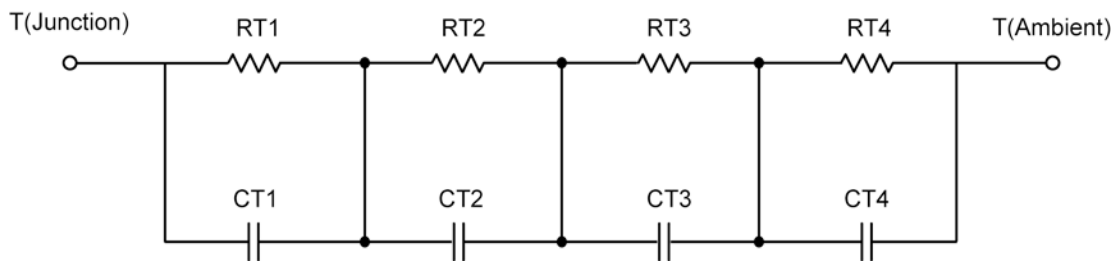
### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*  
For a detailed explanation of implementing these values in P-SPIICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPIICE Platform](#).

### R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	N/A	32.5705 m	N/A
RT2	N/A	59.8803 m	N/A
RT3	N/A	91.5983 m	N/A
RT4	N/A	316.6188 m	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	N/A	676.1971 m	N/A
CT2	N/A	160.4 727 m	N/A
CT3	N/A	12.8460 m	N/A
CT4	N/A	121.3320 m	N/A

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*



## R-C THERMAL MODEL FOR FILTER CONFIGURATION



<b>R-C VALUES FOR FILTER CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	N/A	4.7781 m	N/A
RF2	N/A	86.3667 m	N/A
RF3	N/A	130.8067 m	N/A
RF4	N/A	278.4771 m	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	N/A	7.1512 m	N/A
CF2	N/A	3.5445 m	N/A
CF3	N/A	20.2097 m	N/A
CF4	N/A	97.1664 m	N/A

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

